

2MBI800VG-120P

IGBT Modules

IGBT MODULE (V series) 1200V / 800A / 2 in one package

■ Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc= 25°C unless otherwise specified)

Items	Symbols	Conditions		Maximum Ratings	Units	
Collector-Emitter voltage	Vces			1200	V	
Gate-Emitter voltage	V _{GES}			±20	V	
	Ic	Continuous	Tc=25°C	1200		
			Tc=100°C	800		
Collector current	I _{cp}	1ms	Tc=100°C	1600	Α	
	-I _c	1ms		800		
	-Ic pulse			1600		
Collector Power Dissipation	Pc	1 device		5170	W	
Junction temperature	Tj			175		
Operating junction temperature(under switching conditions)	Tjop			150	°C	
Storage temperature	T _{stg}			-40 ~ +150		
Isolation voltage between terminal and copper base *1	Viso	AC : 1min.		4000	VAC	
	Mounting	M6 M8		5.75	N m	
Screw Torque *2	Main Terminals			10		
·	Sense Terminals	M4		2.5		

^(*1) All terminals should be connected together when isolation test will be done. (*2) Recommendable Value :Mounting 4.25~5.75 Nm (M6) , Main Terminals 8~10 Nm (M8) , Sense Terminals 1.7~2.5 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Itama	Cumbala	Symbols Conditions		Characteristics			I In:ita	
Items	Symbols			min.	typ.	max.	Units	
Zero gate voltage Collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	1.0	mA	
Gate-Emitter leakage current	Iges	Vce = 0V, Vge=±20V		-	-	1600	nA	
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _c = 800mA		6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	V _{CE} (sat)	V _{GE} = 15V Ic = 800A	T _j =25°C	-	1.91	2.19	V	
	(main		T _j =125°C	-	2.21	-		
	terminal)		T _j =150°C	-	2.31	-		
	V		T _j =25°C	-	1.70	1.95		
	V _{CE} (sat)		T _i =125°C	-	2.00	-		
	(chip)		T _j =150°C	-	2.10	-		
Internal gate resistance	Int Rg	-		-	2.19	-	Ω	
Input capacitance	Cies	Vce=10V,Vge=0V,f=1MHz		-	70	-	nF	
Turn-on	t on	V _{cc} = 600V		-	1.97	-		
		tr Ic = 800A L _m = 75nH		-	0.70	-		
	Tr .			-	0.70	-		
Turn-off	toff	V _{GE} = ±15V , T _j = 125°C		-	1.33	-	– μs	
	tr	$R_{gon} = 2.4 \Omega$ $R_{goff} = 0.22 \Omega$		-	0.15	-		
Forward on voltage	VF		T _j =25°C	-	1.91	2.19	V	
	(main	V _{GE} = 0V I _F = 800A	T _i =125°C	-	2.06	-		
	terminal)		T _i =150°C	-	2.01	-		
	.,		T _i =25°C	-	1.70	1.95		
	V _F		T _j =125°C	-	1.85	-		
	(chip)		T _i =150°C	-	1.80	-		
Reverse recovery	trr	I _F = 800A , T _j = 125°C	, ,	-	0.31	-	μs	
Lead resistance, terminal-chip	Rlead	-		-	0.268		mΩ	

● Thermal resistance characteristics

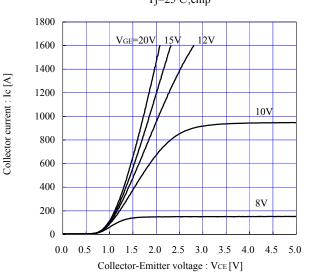
Items	Symbols	Conditions	Characteristics			Units
items	Syllibols	Conditions	min.	typ.	max.	Units
Thermal resistance	Rth(j-c)	IGBT	-	-	0.0290	°C/W
	Ku(j-c)	FWD	-	-	0.0460	
Contact thermal resistance	R _{th(c-f)}	with Thermal Compound(*)	-	0.0060	-	

^{*}This is the value which is defined mounting on the additional cooling fin with thermal compound.

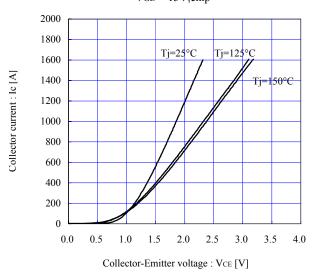
■ Characteristics (Representative)

Collector current vs. Collector-Emitter voltage (typ.)

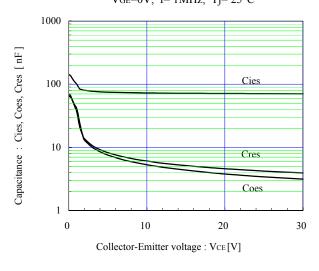
Tj=25°C,chip



 $\label{eq:collector-Emitter voltage vs. Gate-Emitter voltage (typ.)} $$V_{GE}=+15V, chip$$

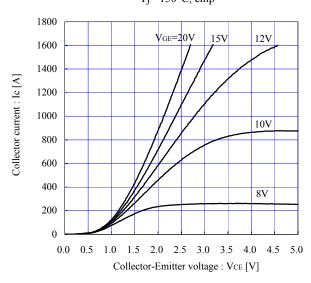


Capacitance vs. Collector-Emitter voltage (typ.) $V_{GE}=0V$, f= 1MHz, $T_{j}=25^{\circ}C$

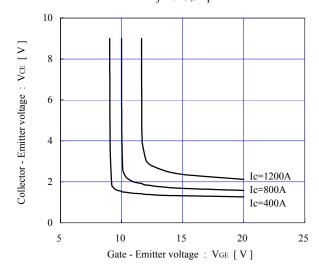


Collector current vs. Collector-Emitter voltage (typ.)

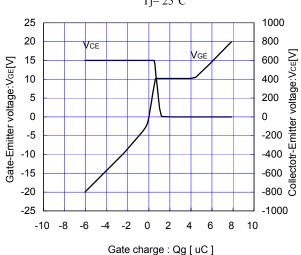
Tj= 150°C, chip



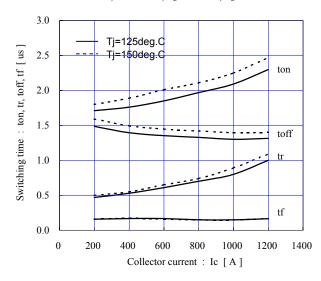
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj=25°C,chip



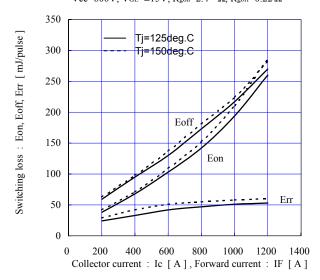
Dynamic Gate charge (typ.) Tj= 25°C



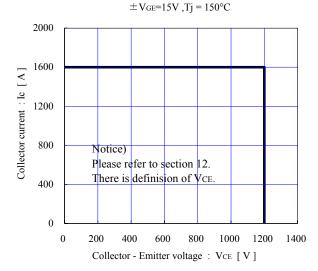




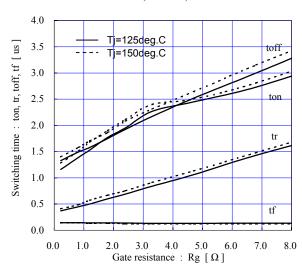
Switching loss vs. Collector current (typ.) Vcc=600V, VGE= \pm 15V, Rgon=2.4 Ω , Rgofi=0.22 Ω



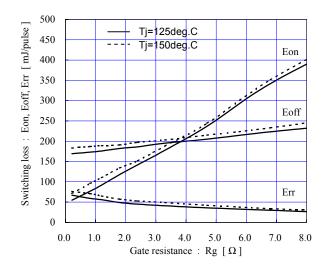
Reverse bias safe operating area (max.)



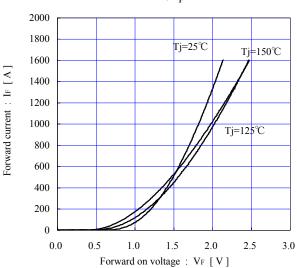
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=800A, V_{GE}=±15V



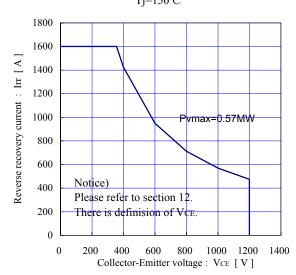
Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=800A, VGE=±15V



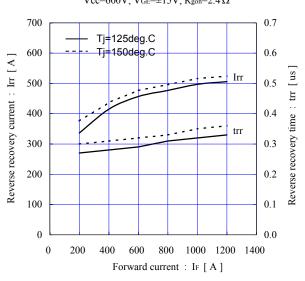
Forward current vs. Forward on voltage (typ.) chip



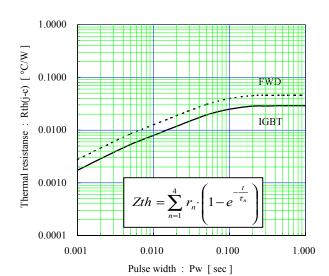
FWD safe operating area (max.) $\label{eq:total_problem} Tj{=}150^{\circ}\!C$



Reverse recovery characteristics (typ.) Vcc=600V, $V_{GE}=\pm15V$, $R_{gon}=2.4\Omega$

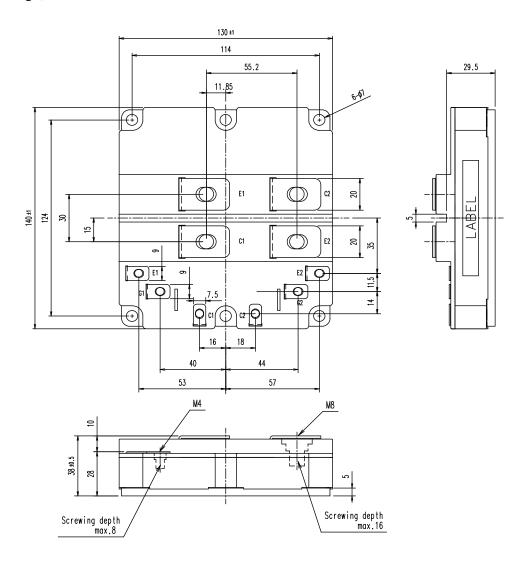


Transient thermal resistance (max.)

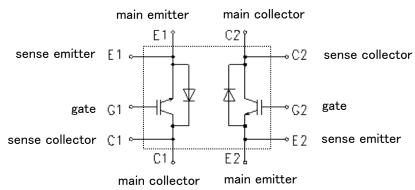


	IGBT	FWD
r1	0.00311	0.00494
r2	0.00851	0.01350
r3	0.01028	0.01630
r4	0.00710	0.01127
τ1	0.0023	0.0023
τ2	0.0310	0.0310
τ3	0.0623	0.0623
τ4	0.0682	0.0682

■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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